



功率半导体芯片 | Power Semiconductor Chips



» 晶闸管芯片 | Thyristor Chips

标准:

- 每片芯片全部在 T_{JM} 下测试, 严格禁止抽检
- 产品参数一致性极佳

Standard:

- Every chips are tested at T_{JM} , random inspections are strictly prohibited.
- Excellent consistency of the chips' parameters

特点:

- 通态压降低
- 具有很强的抗热疲劳能力
- 阴极铝层厚度 10 微米以上
- 台面双层保护

Features:

- Low forward voltage
- Strong thermal fatigue resistance
- The thickness of cathode aluminum layer is above $10\mu m$
- Double layer protections on mesa



芯片直径	芯片厚度	电压范围	门极直径	阴极内径	阴极外径	结温
Diameter	Thickness	Voltage	Gate Dia.	Cathode Inner Dia.	Cathode Out Dia.	T_{jm}
mm	mm	V	mm	mm	mm	$^{\circ}C$
25.4	1.5 ± 0.1	≤ 2000	2.5	5.6	20.3	125
	1.6~1.8	2200~3500	2.6	5.6	15.9	125
29.72	2 ± 0.1	≤ 2000	3.3	7.7	24.5	125
32	2 ± 0.1	≤ 2000	3.3	7.7	26.1	125
35	2 ± 0.1	≤ 2000	3.8	7.6	29.1	125
	2.1~2.4	2200~4200	3.8	7.6	24.9	125
38.1	2 ± 0.1	≤ 2000	3.3	7.7	32.8	125
40	2 ± 0.1	≤ 2000	3.3	7.7	33.9	125
	2.1~2.4	2200~4200	3.5	8.1	30.7	125
45	2.3 ± 0.1	≤ 2000	3.6	8.8	37.9	125
50.8	2.5 ± 0.1	≤ 2000	3.6	8.8	43.3	125
	2.6~2.9	2200~4200	3.8	8.6	41.5	125
	2.6~2.8	2600~3500	3.3	7	41.5	125
55	2.5 ± 0.1	≤ 2000	3.3	8.8	47.3	125
	2.5~2.9	≤ 4200	3.8	8.6	45.7	125
60	2.6~3.0	≤ 4200	3.8	8.6	49.8	125
63.5	2.7~3.1	≤ 4200	3.8	8.6	53.4	125
70	3.0~3.4	≤ 4200	5.2	10.1	59.9	125
76	3.5~4.1	≤ 4800	5.2	10.1	65.1	125
89	4~4.4	≤ 4200	5.2	10.1	77.7	125
99	4.5~4.8	≤ 3500	5.2	10.1	87.7	125